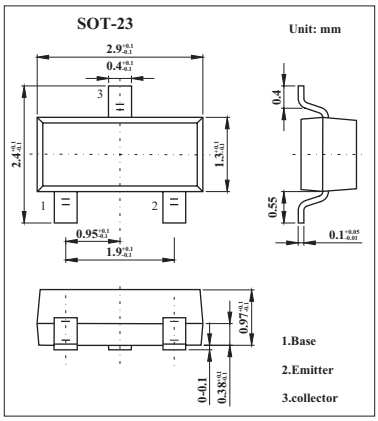
Silicon NPN Epitaxial Planar Type

2SC3125



■ Features

- Good Lineality of fT

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	50	mA
Base current	I_B	25	mA
Collector Power Dissipation	P_C	150	mW
Junction temperature	T_j	125	℃
Storage temperature Range	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 30V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 3V, I_C = 0			1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	25			V
DC current gain	h_{FE}	V_{CE} = 10 V, I_C = 10mA	20	70	200	
Saturation Voltage Collector-Emitter	$V_{CE(sat)}$	I_C=15mA,I_B=1.5mA			0.2	V
Saturation Voltage Baser-Emitter	$V_{BE(sat)}$				1.5	V
Transition Frequency	f_T	V_{CE} = 10 V, I_C = 10mA	250	600		MHz
Collector Output Capacitance	Cob	V_{CC}=10V,I_E=0,f=1MHz		1.1	1.6	pF
Collector-BaseTime Constant	$C_{c.rbb'}$	V_{CB}=10V,I_C=1mA,f=30MHz			25	ps

■ Marking

Marking	HH